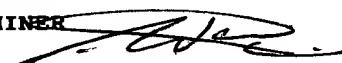


Sheet 1 of 1								Atty. Docket No. 3905	Serial No.: 09/519,408				
FIFTH LIST OF REFERENCES CITED BY APPLICANT (REVISED FORM PTO-1449) DATED: December 27, 2002								Applicant: Takao NAKAMURA et al.					
								U.S. Filing Date: March 3, 2000 CPA FILED: 03/18/02	Art Unit: 2814				
U. S. PATENT DOCUMENTS													
*EXAMINER INITIAL		DOCUMENT NO.						DATE	NAME	Cl.	Sub- Cl.	Fil. Date	
WSL	AC2	5	4	1	1	7	7	2	05/1995	Cheung	-	-	-
FOREIGN PATENT DOCUMENTS										Trans.			
		DOCUMENT NO.						DATE	COUNTRY				Cl.
WSL	AD2	11	1	1	9	2	3	8	04/1999	Japan	-	-	Computer Translation + Abstract
OTHER DOCUMENTS													
EXAMINER					DATE CONSIDERED					1/24/03			
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Sheet 1 of 2								Atty. Docket No. 3905	Serial No.: 09/519,408					
FOURTH LIST OF REFERENCES CITED BY APPLICANT (REVISED FORM PTO-1449) DATED: <u>June 18, 2002</u>								Applicant: Takao NAKAMURA et al.						
								U.S. Filing Date: March 3, 2000 CPA FILED: 03/18/02	Art Unit: 2811					
U. S. PATENT DOCUMENTS														
*EXAMINER INITIAL		DOCUMENT NO.				DATE	NAME		Cl.	Sub-Cl.	Fil. Date			
									-	-	-			
FOREIGN PATENT DOCUMENTS										Trans.				
		DOCUMENT NO.				DATE	COUNTRY	Cl.	Sub-Cl.	Yes	No			
WSL	AE	57	0	9	7	6	8	6	06/1982	Japan	-	-	x-Abstract	
	AF	57-	1	0	6	2	4	6	06/1982	Japan	Utility Model	-	-	x-Par. Trans.
	AG	58	1	6	2	0	7	6	09/1983	Japan	-	-	x-Abstract	
	AR	W092	/	2	1	1	7	0	11/1992	PCT	-	-	x	
	AI	05	1	3	6	4	5	8	06/1993	Japan	-	-	x-Abstract	
	AJ	05	2	8	3	7	4	6	10/1993	Japan	-	-	x-Abstract	
	AK	6-	5	0	8	0	0	3	09/1994	Japan	-	-	x=AH	
	AL	06	2	8	3	4	3	3	10/1994	Japan	-	-	x-Abstract	
	AM	08	1	0	2	5	4	8	04/1996	Japan	-	-	x-Abstract	
	AN	10	0	1	2	9	2	1	01/1998	Japan	-	-	x-Abstract	
	AO	10	0	7	4	5	8	6	03/1998	Japan	-	-	x-Abstract	
	AP	10	2	0	0	1	6	3	07/1998	Japan	-	-	x-Abstract	
	AQ	10	3	0	8	5	3	4	11/1998	Japan	-	-	x-Abstract	
	AR	11	0	8	7	7	7	2	03/1999	Japan	-	-	x-Abstract	
	AS	11	1	2	1	8	0	4	04/1999	Japan	-	-	x-Abstract	
	AT	2000	1	9	6	1	5	2	07/2000	Japan	-	-	x=Abstract	
OTHER DOCUMENTS														
EXAMINER 					DATE CONSIDERED 									
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Sheet <u>2</u> of <u>2</u>								Atty. Docket No. 3905	Serial No.: 09/519,408					
LIST OF REFERENCES CITED BY APPLICANT (REVISED FORM PTO-1449) DATED: June 18, 2002								Applicant: Takao NAKAMURA et al.						
								U.S. Filing Date: March 3, 2000 CPA FILED: 03/18/02	Art Unit: 2811					
U. S. PATENT DOCUMENTS														
*EXAMINER INITIAL		DOCUMENT NO.				DATE	NAME		Cl.	Sub- Cl.	Fil. Date			
FOREIGN PATENT DOCUMENTS										Trans.				
		DOCUMENT NO.				DATE	COUNTRY	Cl.	Sub- Cl.	Yes	No			
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WSL	AV	Y. Fan et al.; "Graded band gap ohmic contact to p-ZnSe"; Appl. Phys. Lett. 61 (26), 28 December 1992, 1992 American Institute of Physics, pages 3160 to 3162.												
	AW	E. Masetti et al.; "Analysis of the oxidation of polycrystalline zinc selenide by spectroscopic ellipsometry and photothermal deflection spectroscopy", Thin Solid Films, 234 (1993), pages 557 - 560.												
	AX	In2O3-ZnO-based Amorphous Transparent Conductive Film (IDIXO); Display Monthly and partial English translation thereof, 3/1998, pages 15 to 20.												
	AY	S. J. Pearton et al.; "Ion implantation doping and isolation of GaN", Appl. Phys. Lett. 67 (10), 4. September, 1995, 1995 American Institute of Physics, pages 1435 to 1437.												
	AZ	J. B. Smathers et al.; "Nanometer scale surface clustering on ZnSe epilayers"; Applied Physics Letters, Volume 72, Number 10, March 9, 1998; pages 1238 to 1240.												
	AA2	A. Waag et al.; "Novel beryllium containing II-VI compounds: basic properties and potential applications"; Journal of Crystal Growth 184/185 (1998), pages 1 to 10.												
	AB2	Stephen J. Pearton; "GaN and Related Materials II", Gordon and Breach Science Publishers, 2000; pgs. 52, 88.												
EXAMINER					DATE CONSIDERED						7/29/02			
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